

CDSV6-16-G/4148-G

Forward Current: 0.15A

Reverse Voltage: 75V

RoHS Device

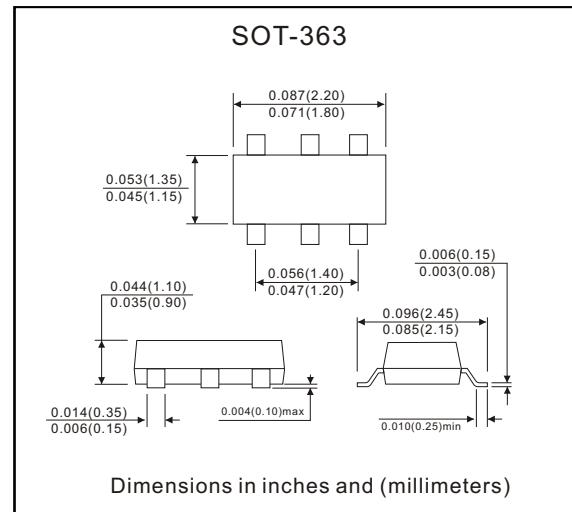
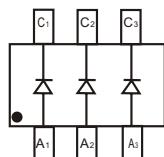


Features

- Fast switching speed.
- For general purpose switching applications.
- High conductance.

Marking: KA2

Diagram:



Maximum Rating (at TA=25°C unless otherwise noted)

| Parameter | Symbol | Limits | Unit |
|---|--|------------|------|
| Non-repetitive peak reverse voltage | V _{RM} | 100 | V |
| Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage | V _{RRM} V _{RWM} V _R | 75 | V |
| RMS reverse voltage | V _{R(RMS)} | 53 | V |
| Forward continuous current | I _{FM} | 300 | mA |
| Averaged rectified output current | I _O | 150 | mA |
| Peak forward surge current @t=1.0μS @t=1.0S | I _{FSM} | 2.0 1.0 | A |
| Power dissipation | P _D | 200 | mW |
| Thermal resistance, junction to ambient air | R _{θJA} | 625 | °C/W |
| Operation and storage temperature range | T _J , T _{STG} | -65 ~ +150 | °C |

Electrical Characteristics (at TA=25°C unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|-------------------------------|--|--|-----|-----|-------------------------------|----------|
| Reverse breakdown voltage | I _R =1μA | V _{(BR)R} | 75 | | | V |
| Forward voltage | I _F =1mA I _F =10mA I _F =50mA I _F =150mA | V _{F1} V _{F2} V _{F3} V _{F4} | | | 0.715 0.855 1.0 1.25 | V |
| Reverse leakage current | V _R =20V V _R =75V | I _{R1} I _{R2} | | | 25 1 | nA μA |
| Capacitance between terminals | V _R =0V, f=1.0MHz | C _T | | | 2 | pF |
| Reverse recovery time | I _F =I _R =10mA to I _{rr} =0.1×I _R , R _L =100Ω | t _{rr} | | | 4 | nS |

SMD Switching Diode Arrays

COMCHIP
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ELECTRICAL CHARACTERISTIC CURVES (CDSV6-16-G/4148-G)

Fig.1 Forward Characteristics

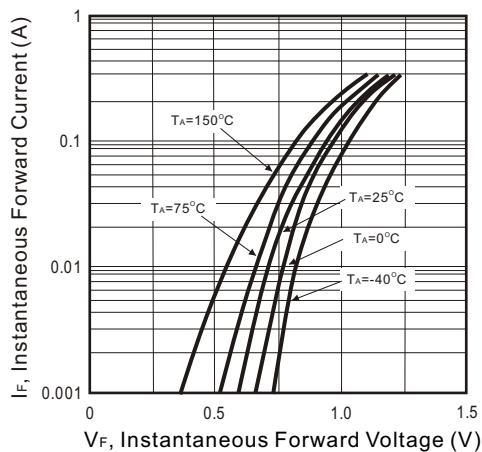


Fig.2 Reverse Characteristics

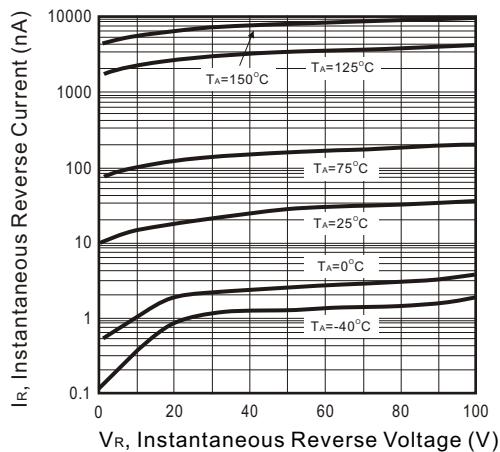


Fig.3 Capacitance Between Terminals Characteristics

